

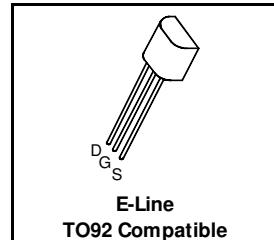
N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 – MARCH 94

ZVN2106A

FEATURES

- * 60 Volt V_{DS}
- * $R_{DS(on)}=2\Omega$



ABSOLUTE MAXIMUM RATINGS.

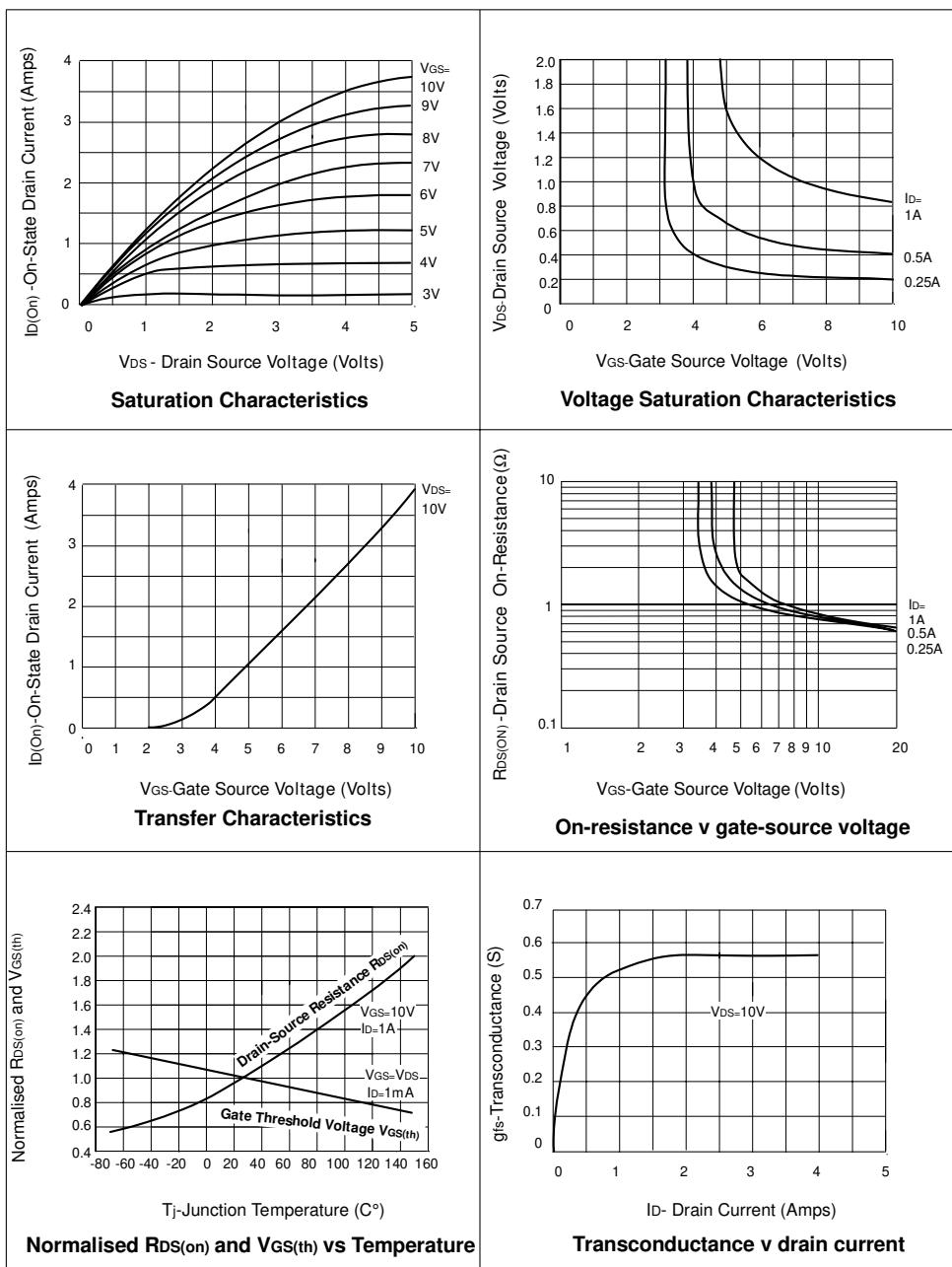
PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current at $T_{amb}=25^\circ C$	I_D	450	mA
Pulsed Drain Current	I_{DM}	8	A
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^\circ C$	P_{tot}	700	mW
Operating and Storage Temperature Range	$T_j \cdot T_{stg}$	-55 to +150	°C

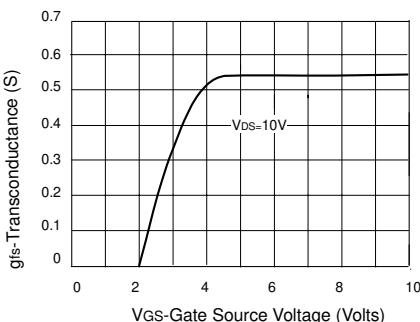
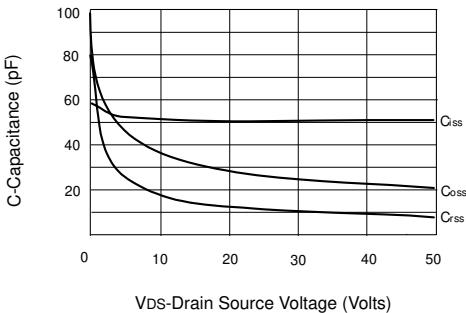
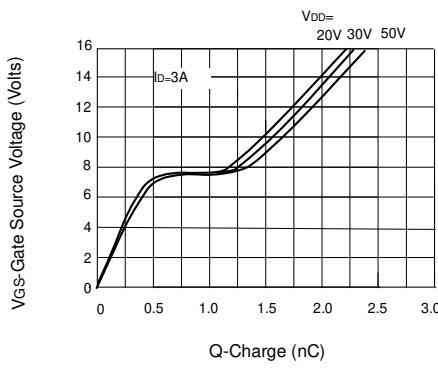
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	60		V	$I_D=1mA$, $V_{GS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.8	2.4	V	$ID=1mA$, $V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}		20	nA	$V_{GS}=\pm 20V$, $V_{DS}=0V$
Zero Gate Voltage Drain Current	I_{DSS}		500 100	nA μA	$V_{DS}=60 V$, $V_{GS}=0$ $V_{DS}=48 V$, $V_{GS}=0V$, $T=125^\circ C(2)$
On-State Drain Current(1)	$I_{D(on)}$	2		A	$V_{DS}=18V$, $V_{GS}=10V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		2	Ω	$V_{GS}=10V$, $I_D=1A$
Forward Transconductance (1)(2)	g_{fs}	300		mS	$V_{DS}=18V$, $I_D=1A$
Input Capacitance (2)	C_{iss}		75	pF	$V_{DS}=18 V$, $V_{GS}=0V$, $f=1MHz$
Common Source Output Capacitance (2)	C_{oss}		45	pF	
Reverse Transfer Capacitance (2)	C_{rss}		20	pF	

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TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS**Transconductance v gate-source voltage****Capacitance v drain-source voltage****Gate charge v gate-source voltage**